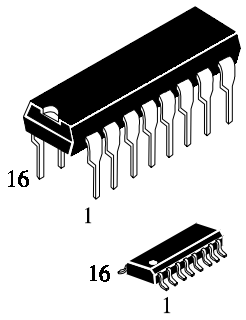
IN74HC4015

Dual 4-Bit Shift Register
High-Performance Silicon-Gate CMOS



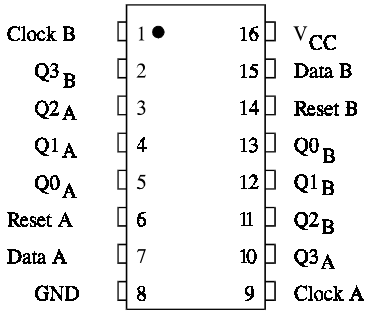
ORDERING INFORMATION
IN74HC4015N Plastic
IN74HC4015D SOIC
T_A = -55° to 125° C for all packages

The device inputs are compatible with standard CMOS outputs; with pullup resistors, they are compatible with LS/ALSTTL outputs.

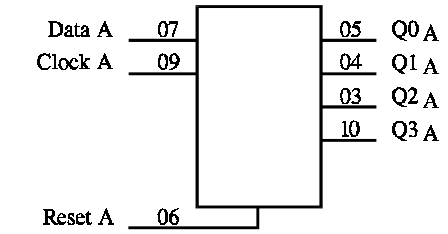
This device consists of two identical independent 4-stage serial-input/parallel-output registers. Each register has independent Clock and Reset inputs as well as a single serial Data input. "Q" outputs are available from each of the four stages on both registers. All register stages are D-type, master-slave flip-flops. The logic level present at the Data input is transferred into the first register stage and shifted over one stage at each positive-going clock transition. Resetting of all stages is accomplished by a high level on the reset line.

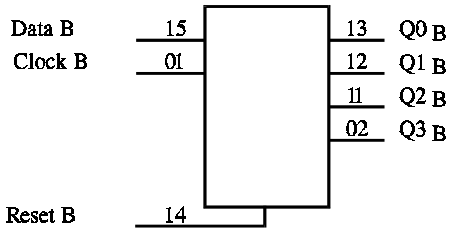
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 2.0 to 6.0 V
- Low Input Current: 1.0 μA
- High Noise Immunity Characteristic of CMOS Devices

PIN ASSIGNMENT



LOGIC DIAGRAM





PIN 16 = V_{CC}
PIN 8 = GND

FUNCTION TABLE

Inputs			Outputs	
Clock	Data	Reset	Q_0	Q_n
⌐	L	L	L	Q_{n-1}
⌐	H	L	H	Q_{n-1}
¬	X	L	Q_0*	Q_n*
X	X	H	L	L

* = No Change
X = don't care

INTEGRAL

MAXIMUM RATINGS*

Symbol	Parameter	Value	Unit
V_{CC}	DC Supply Voltage (Referenced to GND)	-0.5 to +7.0	V
V_{IN}	DC Input Voltage (Referenced to GND)	-1.5 to V_{CC} +1.5	V
V_{OUT}	DC Output Voltage (Referenced to GND)	-0.5 to V_{CC} +0.5	V
I_{IN}	DC Input Current, per Pin	±20	mA
I_{OUT}	DC Output Current, per Pin	±25	mA
I_{CC}	DC Supply Current, V_{CC} and GND Pins	±50	mA
P_D	Power Dissipation in Still Air, Plastic DIP+ SOIC Package+	750 500	mW
Tstg	Storage Temperature	-65 to +150	°C
T_L	Lead Temperature, 1 mm from Case for 10 Seconds (Plastic DIP or SOIC Package)	260	°C

*Maximum Ratings are those values beyond which damage to the device may occur.
Functional operation should be restricted to the Recommended Operating Conditions.
+Derating - Plastic DIP: - 10 mW/°C from 65° to 125°C
SOIC Package: : - 7 mW/°C from 65° to 125°C

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Min	Max	Unit
V_{CC}	DC Supply Voltage (Referenced to GND)		2.0	6.0	V
V_{IN}, V_{OUT}	DC Input Voltage, Output Voltage (Referenced to GND)		0	V_{CC}	V
T_A	Operating Temperature, All Package Types		-55	+125	°C
t_r, t_f	Input Rise and Fall Time (Figure 1)	V_{CC} =2.0 V V_{CC} =4.5 V V_{CC} =6.0 V	0 0 0	1000 500 400	ns

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, V_{IN} and V_{OUT} should be constrained to the range GND≤(V_{IN} or V_{OUT})≤V_{CC}.

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

DC ELECTRICAL CHARACTERISTICS(Voltages Referenced to GND)

Symbol	Parameter	Test Conditions	V_{CC} V	Guaranteed Limit			Unit
				25 °C to -55°C	≤85 °C	≤125 °C	
V_{IH}	Minimum High-Level Input Voltage	V_{OUT}= 0.1 V or V_{CC}-0.1 V $\|I_{OUT}\| \leq 20$ μA	2.0 4.5 6.0	1.5 3.15 4.2	1.5 3.15 4.2	1.5 3.15 4.2	V
V_{IL}	Maximum Low - Level Input Voltage	V_{OUT}=0.1 V or V_{CC}-0.1 V $\|I_{OUT}\| \leq 20$ μA	2.0 4.5 6.0	0.3 0.9 1.2	0.3 0.9 1.2	0.3 0.9 1.2	V
V_{OH}	Minimum High-Level Output Voltage	V_{IN}=V_{IH} or V_{IL} $\|I_{OUT}\| \leq 20$ μA	2.0 4.5 6.0	1.9 4.4 5.9	1.9 4.4 5.9	1.9 4.4 5.9	V
		V_{IN}= V_{IH} or V_{IL} $\|I_{OUT}\| \leq 4.0$ mA $\|I_{OUT}\| \leq 5.2$ mA	 4.5 6.0	 3.98 5.48	 3.84 5.34	 3.7 5.2	
V_{OL}	Maximum Low-Level Output Voltage	V_{IN}=V_{IH} or V_{IL} $\|I_{OUT}\| \leq 20$ μA	2.0 4.5 6.0	0.1 0.1 0.1	0.1 0.1 0.1	0.1 0.1 0.1	V
		V_{IN}= V_{IH} or V_{IL} $\|I_{OUT}\| \leq 4.0$ mA $\|I_{OUT}\| \leq 5.2$ mA	 4.5 6.0	 0.26 0.26	 0.33 0.33	 0.4 0.4	
I_{IN}	Maximum Input Leakage Current	V_{IN}=V_{CC} or GND	6.0	±0.1	±1.0	±1.0	μA
I_{CC}	Maximum Quiescent Supply Current (per Package)	V_{IN}=V_{CC} or GND I_{OUT}=0μA	6.0	8.0	80	160	μA

AC ELECTRICAL CHARACTERISTICS(C_L=50pF,Input t_r=t_f=6.0 ns)

Symbol	Parameter	V_{CC} V	Guaranteed Limit			Unit
			25 °C to -55°C	≤85°C	≤125°C	
f_{max}	Maximum Clock Frequency (50% Duty Cycle) (Figure 2)	2.0 4.5 6.0	6 30 35	4.8 24 28	4 20 24	MHz
t_{PLH}, t_{PHL}	Maximum Propagation Delay, Clock to Q (Figures 2 and 5)	2.0 4.5 6.0	175 35 30	220 44 37	265 53 45	ns
t_{PHL}	Maximum Propagation Delay, Reset to Q (Figures 1 and 5)	2.0 4.5 6.0	205 41 35	255 51 43	310 62 53	ns
t_{TLH}, t_{THL}	Maximum Output Transition Time, Any Output (Figures 3 and 5)	2.0 4.5 6.0	75 15 13	95 19 16	110 22 19	ns
C_{IN}	Maximum Input Capacitance	-	10	10	10	pF

C_{PD}	Power Dissipation Capacitance (Per Latch) Used to determine the no-load dynamic power consumption: $P_D=C_{PD}V_{CC}^2f+I_{CC}V_{CC}$	Typical @25°C,V_{CC}=5.0 V 140	pF

TIMING REQUIREMENTS(C_L=50pF,Input t_r=t_f=6.0 ns)

Symbol	Parameter	V_{CC} V	Guaranteed Limit			Unit
			25 °C to -55°C	≤85°C	≤125°C	
t_{su}	Minimum Setup Time, D to Clock (Figure 4)	2.0 4.5 6.0	50 10 9.0	65 13 11	75 15 13	ns
t_h	Minimum Hold Time, Clock to D (Figure 4)	2.0 4.5 6.0	5 5 5	5 5 5	5 5 5	ns
t_{rec}	Minimum Recovery Time, Reset to Clock (Figure 1)	2.0 4.5 6.0	5 5 5	5 5 5	5 5 5	ns
t_w	Minimum Pulse Width, Reset (Figure 1)	2.0 4.5 6.0	80 16 14	100 20 17	120 24 20	ns
t_w	Minimum Pulse Width, Clock (Figure 4)	2.0 4.5 6.0	80 16 14	100 20 17	120 24 20	ns
t_r, t_f	Maximum Input Rise and Fall Times (Figure 1)	2.0 4.5 6.0	1000 500 400	1000 500 400	1000 500 400	ns

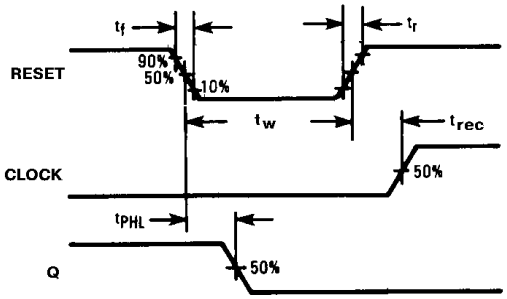


Figure 1. Switching Waveforms

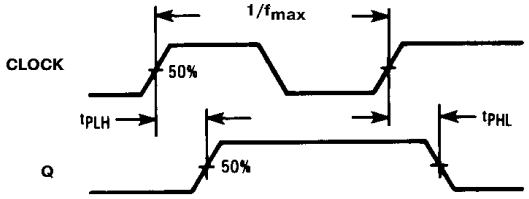


Figure 2. Switching Waveforms

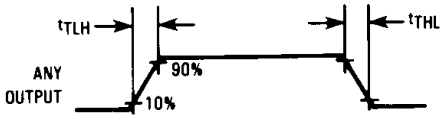


Figure 3. Switching Waveforms

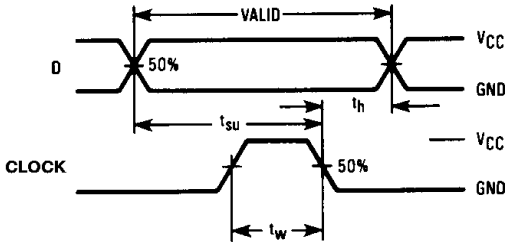


Figure 4. Switching Waveforms

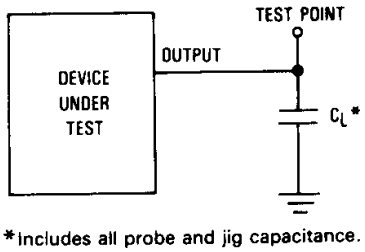


Figure 5. Test Circuit

EXPANDED LOGIC DIAGRAM